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Analysis of GaN and AlN growth on SiC using Synchrotron Radiation.

High-resolution and high surface-sensitive in-situ core-level photoelectron spectra will be presented and briefly discussed.
The main purpose of the work is to study the intricate and complex phenomena occurring at the surface and interface during the growth mechanism of Ga, Al, GaN on SiC, including the analysis of heterostructures. All the processes are followed in-situ by photoelectron spectroscopy using synchrotron radiation.

To have an overview and reasonable understanding of the several processes involved, a careful fitting and chemical state assignments and detailed analysis of core-level spectra are of great importance. For that purpose, FitXps and Casa XPS are employed.

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